

NCE P-Channel Enhancement Mode Power MOSFET

Description

The NCE60P12K uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge .This device is well suited for high current load applications.

General Features

V_{DS} =-60V,I_D =-12A

 $R_{DS(ON)}$ <100m Ω @ V_{GS} =-10V

 $R_{DS(ON)}$ <125m Ω @ V_{GS} =-4.5V

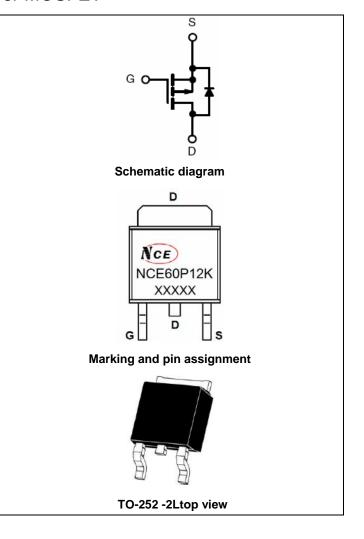
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

- High side switch for full bridge converter
- DC/DC converter for LCD display

100% UIS TESTED!

100% ΔVds TESTED!



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE60P12K	NCE60P12K	TO-252-2L	-	-	-

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	-60	V
Gate-Source Voltage	V _G S	±20	V
Drain Current-Continuous	I _D	-12	Α
Drain Current-Continuous(T _C =100 °C)	I _D (100℃)	-8.5	Α
Pulsed Drain Current	I _{DM}	-30	Α
Maximum Power Dissipation	P _D	60	W
Derating factor		0.4	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	50	mJ
Operating Junction and Storage Temperature Range	T_{J} , T_{STG}	-55 To 175	$^{\circ}$

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NCE60P12K

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	R _{eJC}	2.5	°C/W	Ī
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Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics			•			
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-60	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-60V,V _{GS} =0V	-	-	-1	μΑ
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20 V , V_{DS} =0 V	-	-	±100	nA
On Characteristics (Note 3)			•			
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_D=-250\mu A$	-1	-1.5	-2.2	V
Drain Source On State Desistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-12A	-	84	100	mΩ
Drain-Source On-State Resistance		V _{GS} =-4.5V, I _D =-8A	-	100	125	mΩ
Forward Transconductance	g FS	V _{DS} =-5V,I _D =-12A	-	10	-	S
Dynamic Characteristics (Note4)			•			
Input Capacitance	C _{lss}	\/ 20\/\/ 0\/	-	1630.7	-	PF
Output Capacitance	C _{oss}	V_{DS} =-30V, V_{GS} =0V, F=1.0MHz	-	90.6	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.UMHZ	-	77.3	-	PF
Switching Characteristics (Note 4)	<u>. </u>					
Turn-on Delay Time	$t_{d(on)}$		-	11	-	nS
Turn-on Rise Time	t _r	V_{DD} =-30V, R_L =1.5 Ω , V_{GS} =-10V, R_G =3 Ω	-	14	-	nS
Turn-Off Delay Time	t _{d(off)}		-	33	-	nS
Turn-Off Fall Time	t _f		-	13	-	nS
Total Gate Charge	Qg	V = 20 L = 42A	-	37.6		nC
Gate-Source Charge	Q _{gs}	V_{DS} =-30, I_{D} =-12A, V_{GS} =-10V	-	4.3		nC
Gate-Drain Charge	Q _{gd}	VGS=-10V	-	7.2		nC
Drain-Source Diode Characteristics	<u>. </u>					
Diode Forward Voltage (Note 3)	V_{SD}	V _{GS} =0V,I _S =-12A	-		-1.2	V
Diode Forward Current (Note 2)	Is		-	-	-12	Α
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF =- 12A	-	35		nS
Reverse Recovery Charge	Qrr	$di/dt = -100A/\mu s^{(Note3)}$	-	38		nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negl	igible (tur	n-on is do	minated by	/ LS+LD)

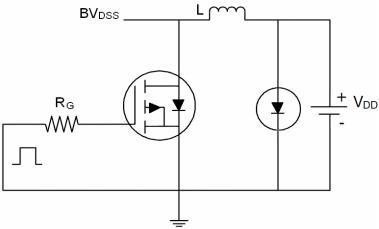
Notes:

- $\textbf{1.} \ \textbf{Repetitive Rating: Pulse width limited by maximum junction temperature.}$
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- **5.** E_{AS} condition: Tj=25 $^{\circ}$ C,V_{DD}=-20V,V_G=-10V,L=1mH,Rg=25 Ω

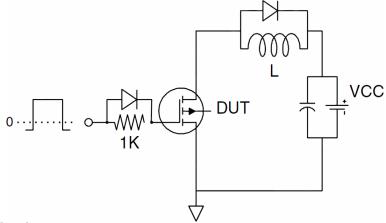


Test Circuit

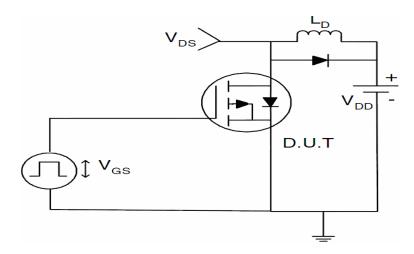
1) E_{AS} Test Circuit



2) Gate Charge Test Circuit



3) Switch Time Test Circuit







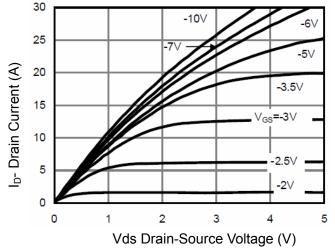


Figure 1 Output Characteristics

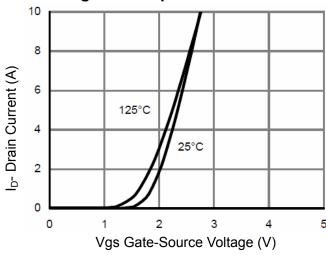


Figure 2 Transfer Characteristics

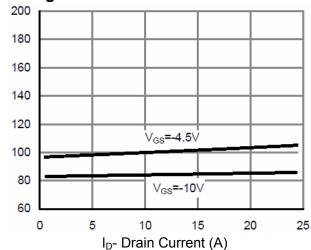


Figure 3 Rdson- Drain Current

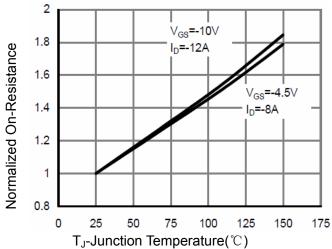


Figure 4 Rdson-Junction Temperature

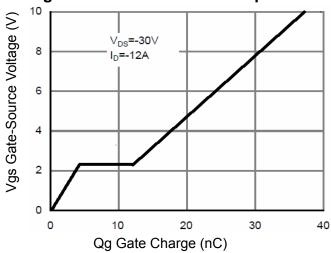


Figure 5 Gate Charge

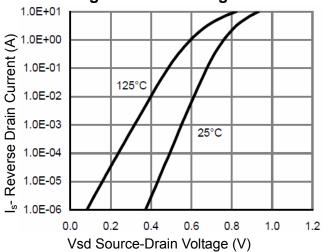
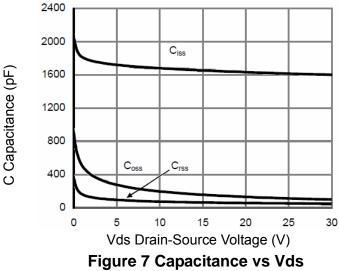


Figure 6 Source- Drain Diode Forward





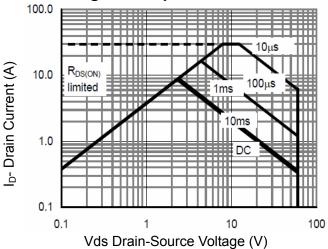


Figure 8 Safe Operation Area

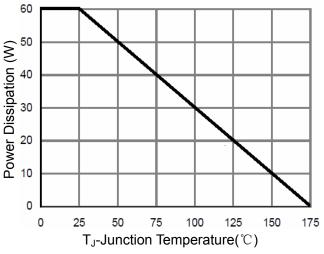


Figure 9 Power De-rating 14 12 10 Ip- Drain Current (A) 8 6 4 2 0 0 25 50 75 100 125 150 175 T_J -Junction Temperature($^{\circ}$ C)

Figure 10 ID Current De-rating

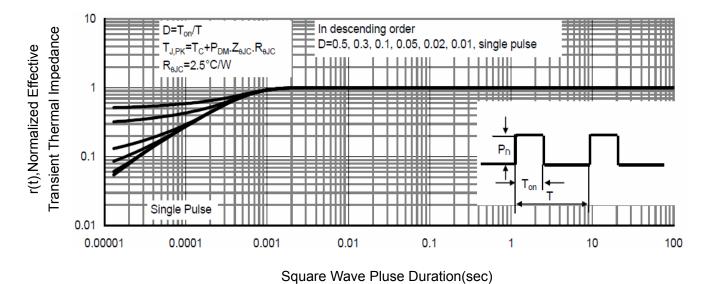
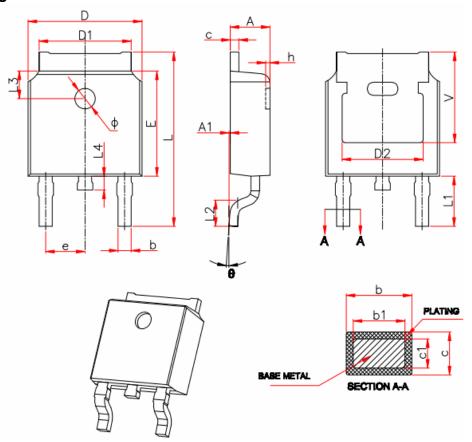


Figure 11 Normalized Maximum Transient Thermal Impedance



TO-252 Package Information



Symbol	Millimeters			
Syllibol	Min.	Max.		
Α	2.20	2.40		
A1	0.00	0.13		
b	0.66	0.86		
b1	0.73	0.79		
С	0.46	0.58		
c1	0.50	0.52		
D	6.50	6.70		
D1	5.10	5.46		
D2	4.83 REF.			
Е	6.00	6.20		
е	2.19	2.39		
L	9.80	10.40		
L1	2.90 REF.			
L2	1.40	1.70		
L3	1.60 REF.			
L4	0.60	1.00		
Ф	1.10	1.30		
θ	0°	8°		





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